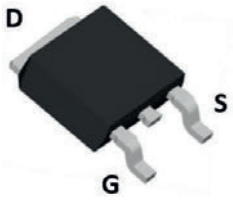
GOOD-ARK SEMICONDUCTOR

GSFD4027

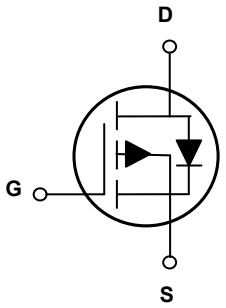
40V P-Channel MOSFET

Main Product Characteristics

BV_{DSS}	-40V
$R_{DS(ON)}$	27mΩ (Max.)
I_D	-32A



TO-252 (DPAK)



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery

RoHS Compliant

Description

The GSFD4027 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous (T_C=25°C), V_{GS}=10V[1]	I_D	-32	A
Drain Current-Continuous (T_C=100°C), V_{GS}=10V[1]		-26	A
Drain Current-Pulsed[2]	I_{DM}	-128	A
Pulsed Source Current (Body Diode)[2]	I_{SM}	-128	A
Power Dissipation (T_C=25°C)[3]	P_D	38	W
Single Pulse Avalanche Energy (L=0.5mH)	E_{AS}	100	mJ
Single Pulse Avalanche Current (L=0.5mH)	I_{AS}	20	A
Thermal Resistance, Junction-to-Ambient (t ≤ 10s)[4]	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.29	°C/W
Operating Junction Temperature Range	T_J	-55 To +150	°C
Storage Temperature Range	T_{STG}	-55 To +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250uA	-40	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	V_{DS}=-40V, V_{GS}=0V	-	-	-1	μA
Drain-to-Source Leakage Current		V_{DS}=-40V, V_{GS}=0V, T_J=125°C	-	-	-50	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=-250uA	-1.1	-	-2.5	V
Drain Static-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-8A	-	22	27	mΩ
		V_{GS}=-4.5V, I_D=-4A	-	27	39	mΩ
Dynamic and Switching Characteristics						
Total Gate Charge	Q_g	V_{DD}=-20V, I_D=-5A, V_{GS}=-10V	-	26	-	nC
Gate-Source Charge	Q_{gs}		-	6.6	-	
Gate-Drain Charge	Q_{gd}		-	3.6	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-20V, R_G=3Ω, V_{GS}=-10V, I_D=-5A	-	7.7	-	nS
Rise Time	t_r		-	4.1	-	
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	
Fall Time	t_f		-	6.0	-	
Input Capacitance	C_{iss}	V_{DS}=-20V, V_{GS}=0V, F=1MHz	-	1421	-	pF
Output Capacitance	C_{oss}		-	128	-	
Reverse Transfer Capacitance	C_{rss}		-	88	-	
Gate Resitance	R_g	F=1MHz	-	9.8	-	Ω
Source-Drain Ratings and Characteristics						
Maximum Body-Diode Continuous Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	-32	A
Maximum Body-Diode Pulse Current	I_{SM}		-	-	-128	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-5A, T_J=25°C	-	-1.0	-1.2	V
Reverse Recovery Time	T_{rr}	I_F=-5A, di/dt=100A/μs, T_J=25°C	-	35	-	nS
Reverse Recovery Charge	Q_{rr}		-	39	-	nC

Notes:

1. Calculated continuous current based on maximum allowable junction temperature.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.
4. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

Typical Electrical and Thermal Characteristic Curves

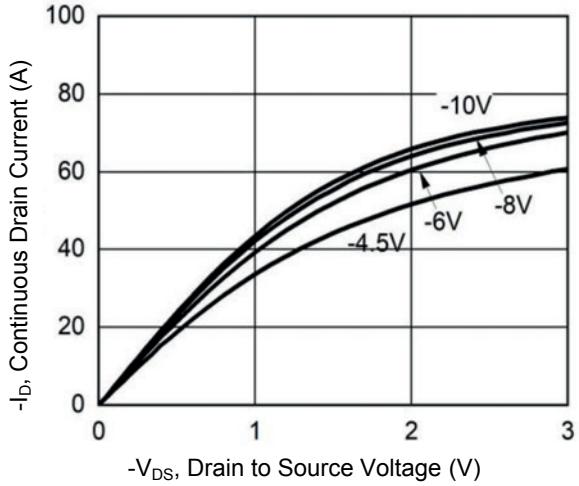


Figure 1. Typical Output Characteristics

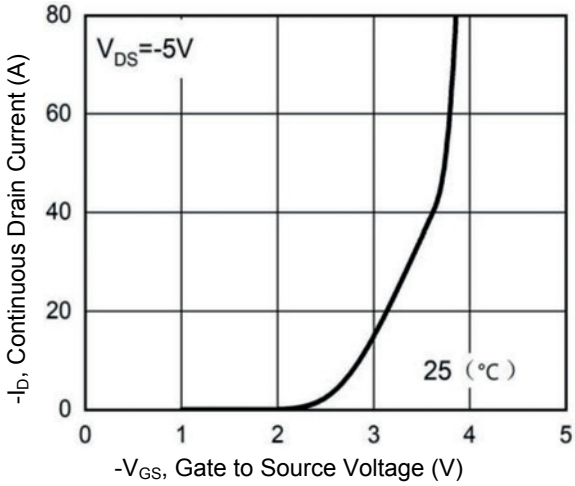


Figure 2. Transfer Characteristics

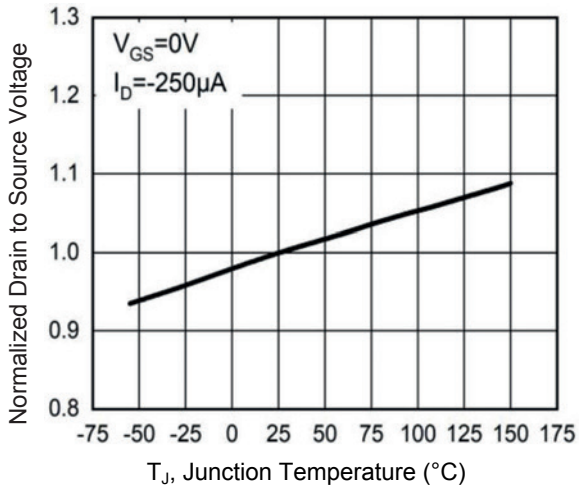


Figure 3. Normalized BV_{DSS} vs. T_J

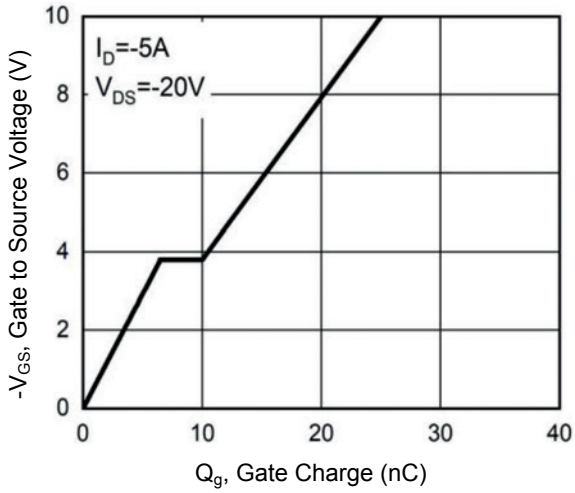


Figure 4. Gate Charge Characteristics

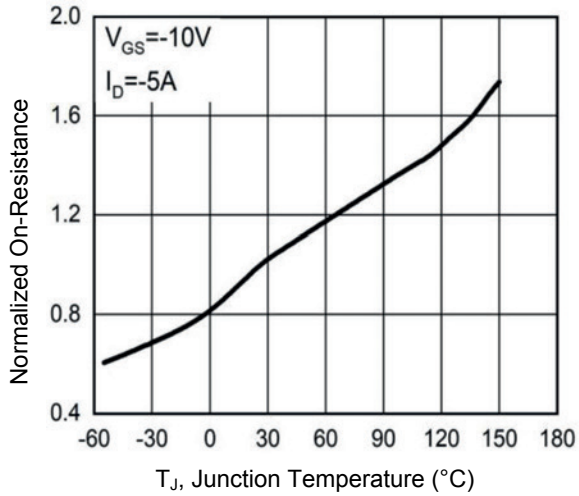


Figure 5. Normalized $R_{DS(ON)}$ vs. T_J

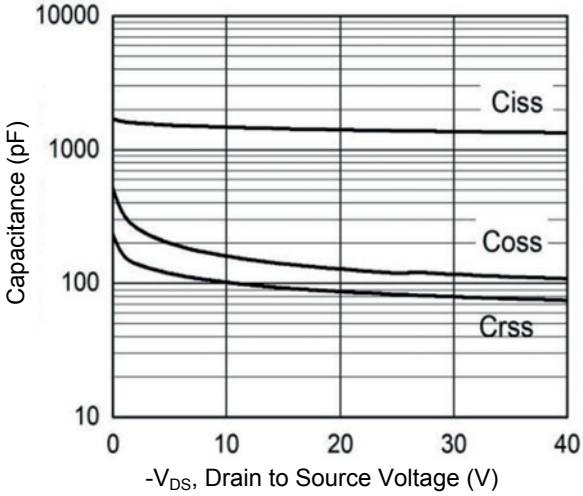


Figure 6. Capacitance Characteristics

Typical Electrical and Thermal Characteristic Curves

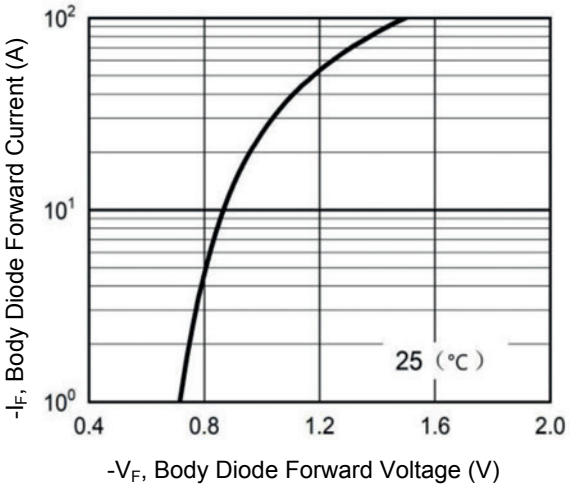


Figure 7. Body Diode Characteristics

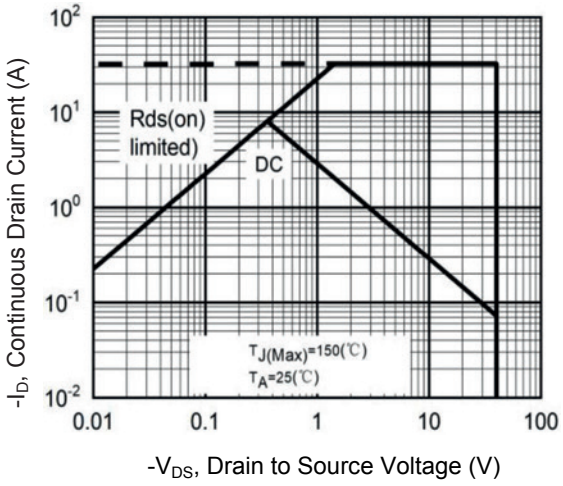
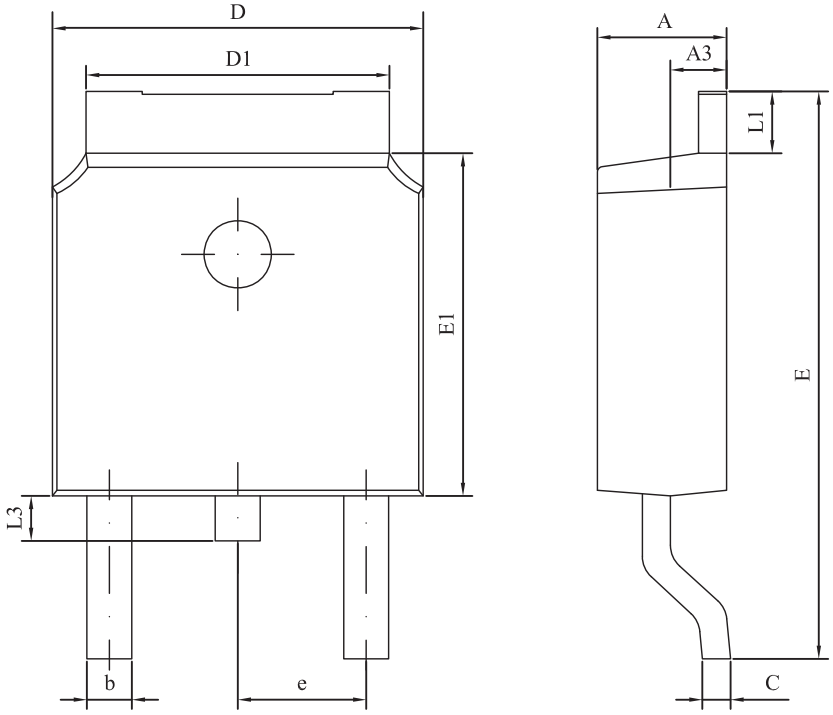


Figure 8. Maximum Safe Operation Area

Package Outline Dimensions TO-252(DPAK)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.40	0.085	0.094
A3	0.90	1.10	0.035	0.043
b	0.50	0.90	0.020	0.035
C	0.40	0.65	0.016	0.026
D	6.30	6.90	0.248	0.272
D1	4.95	5.50	0.195	0.217
E	9.40	10.41	0.370	0.410
E1	5.90	6.30	0.232	0.248
e	2.286 BSC		0.090 BSC	
L1	0.89	1.27	0.035	0.050
L3	0.60	1.10	0.024	0.043

Order Information

Device	Package	Marking	Carrier	Quantity
GSFD4027	TO-252 (DPAK)	D4027	Tape & Reel	2,500pcs / Reel